Abstract

Method for the wet-chemical treatment of a semiconductor wafer

The invention relates to a method for the wet-chemical treatment of a semiconductor wafer, comprising: a) semiconductor wafer is caused to rotate; b) cleaning liquid comprising gas bubbles having a diameter of 100 µm or less is applied to the rotating semiconductor wafer, such that a liquid film forms on the semiconductor wafer; c) the rotating semiconductor wafer is exposed to a gas atmosphere having a reactive gas; d) removing the liquid film.